

View Online at <https://aerobasegroup.com/nsn/5961-01-289-8544>

Inclosure Material:

Metal all transistor

Overall Length:

1.187 inches all transistor

Overall Diameter:

0.610 inches all transistor

End Application:

F-15 acft

Mounting Facility Quantity:

1 all transistor

Internal Configuration:

Junction contact all transistor

Internal Junction Configuration:

Npn all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Threaded stud all transistor

Field Force Effect Type:

Electrostatic charge

Overall Width Across Flats:

0.687 inches all transistor

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

120.0 breakdown voltage, collector-to-base, emitter open all transistor and 90.0 breakdown voltage, collector-to-emitter, base open all transistor and 5.0 breakdown voltage, emitter-to-base, collector open all transistor

Current Rating Per Characteristic:

10.00 milliamperes zero-gate-voltage source current preset all transistor and 10.00 milliamperes zero-gate-voltage source current major all transistor

Test Data Document:

13973-862182 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

3 tab, solder lug all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0